UGAROVA, T.Yu.; TSEYTLIN, P.I.

Effect of desoxyribonucleic acid on the radiosensitivity of --chymotrypsin in an artificial desoxyribonucleic acid. -chymotrypsin complex. Biul. eksp. biol. i med. 50 no.7:55-58 Jl '60.

1. Is Instituta eksperimental'noy biologii (dir. - prof. I.N.Mayskiy) AMN SSSR, Moskva. Predstavlena deystvitel nym chlenom AMN SSSR N.N. AMN SSSN, FROM --Zhukovym-Verezhnikovym.

(RADIATION--PHYSIOLOGICAL EFFECT)

(NIICLEIC ACID)

(CHYMOTRYPSIN) (NUCLEIC ACID)

DISKINA, B. S., and WGAROVA, T. YUL

"A Study of Biological Activity of BNA Bound Proteins. report submitted for the 5th Intl. Congress of Biochemistry, Moscow, 10-16 Aug 1961.

Inst. of Viral Preparations, Moscow.

APPROVED FOR RELEASE: 04/03/2001 CIA-RDP86-00513R001857820011-8"

UGAROVA, T. Yu., DYSKINA, L. S. (USSR).

Examination of the Biological activity of DNA-linked Proteins.

report presented at the 5th Intil.
Biochemistry Congress, Moscow, 10-16 Aug. 1961

ACCESSION NR: AP4015083

8/0205/64/004/001/0047/0051

AUTHOR: Ugarova, T. Yu.; Diskina, B. S.; Tseytlin, P. I.

TITLE: Radiosensitivity of ribonuclease in an artificial DNA-ribonuclease complex

SOURCE: Radiobiologiya, v. 4, no. 1, 1964, 47-51

TOPIC TAGS: ribonuclease radiosensitivity, artificial DNA-ribonuclease complex, X-irradiation, ribonuclease inactivation, free ribonuclease, ribonuclease radiation damage

ABSTRACT: Preparations of ribonuclease mixed with DNA, combined in a DNA complex, and in a free state were X-irradiated (RUT-60 unit, 50 kv, 15 ma, 2000 r/min) with doses ranging from 2 to 30 kr. Ribonuclease radiation damage was determined by decrease in enzyme activity. Artificial DNA-ribonuclease complexes were used in this study because of the heterogeneity of natural DNP protein composition and lack of reliable radiation damage indices. Findings show that X-irradiation inactivates ribonuclease combined in a DNA complex considerably more than in a free state or mixed with DNA. Possible mechanisms which may be responsible for the increased radiosensitivity of ribonuclease Cord 1/2

ACCESSION NR: AP4015083

Several studies of DNA-ribonuclease complexes indicate that approximately 25% of the total number of protein molecules combined with DNA undergo extensive deformation which is accompanied by almost complete loss of protein biological activity. With the ratio between DNA and protein in the artificial complex practically the same as in natural DNP, it appears possible that nucleic acids are inactivated by X-irradiation in a similar manner and this may lead to biological after effects on the chromosome level. Orig. art. has: 2 tables and 1 figure.

ASSOCIATION: Nauchno-issledovatel'skiy institut virusnykh preparatov, Moscow (Scientific-research Institute of Virus Preparations); Institut eksperimental'noy biologii AMN SSSR, Moscow (Institute of Experimental Biology, AMN SSSR)

SUBMITTED: 17Jul63

DATE ACQ: 12Mar64

ENCL: 00

SUB CODE: LS

NO REF SOV: 012

THER: 012

Card 2/2

(MTR 15 11)

WARDVE, T.Yu. DIFFLED, B.S.

Miclogical activity of human and bovine serum protein of the grandeatic ribonuclease in the composition of artificiousy obtained complexes of those proteins with DNA. Birshidt.

29 ep. 5:914-923 Jlate 64.

l. Nauchno-desledovsteliskiy austitut virusnykh proporatov, Moskva.

CATEGORY ARG. JOUR. : EZhBiol., Ne.14, 1998, No. 633335 AUTHOR : Ruebenbauer, T., Ugarynko A. IMST.

TITLE : Comparison of Spring Barley Varieties on the Basis of Experiments Carried Out in Foland During the Years 1950-

1952.

OPIG, FUB. : Roczn. nauk rolniczych, 1956, D 76, 237-354

: Selection of suitable regions for different varieties of ABSTRACT spring barley. A description of 4 groups of varioties is giver. Multi-row varieties of barley (Mazovetskiy and Granum 6-row) and hull-less (Bayskiy) are examined.

Card: 1/1

COUNTRY

35

ACC NR. AP7002735

$$\frac{\partial c}{\partial t} = \frac{\partial}{\partial x} \left(D_{1, \mathbf{d}} \frac{\mathbf{f} \partial c}{\partial x} \right), \tag{1}$$

where c is the concentration of a given $D_{i.d.}$ element at point x at time instant t. Thus the problem of determining the function $D_{i.d.}(c)$ reduces to determining the concentration dependence of elements in the diffusion zone and the accuracy of calculation of $D_{i.d.}$ depends on the accuracy of plotting the curve of c = c(x). It is shown that the method of local x-ray spectral analysis of chemical composition can be used to investigate interdiffusion in the systems Fe-Pd. Co-Pd, Ni-Pd, Cu-Pd over a broad range of temperatures provided that the investigator works only with the radiation of the element for which fluorescent excitation is absent in given binary system. Thus, the distribution of the concentration of investigated elements (such as Fe, Co, Ni) in the diffusion zone of vacuum-welded diffusion pairs can be analyzed according to the radiation of the lines Fe K_{α} , Co K_{α} , and Ni K_{α} , respectively, with the characteristic x-ray spectrum being excited only be electron impact, in a RSASh-2 local x-ray spectrum analyzer. The resulting averaged and corrected curves of concentration are used to calc late the values of $D_{i.d.}(c)$ over the entire range of concentrations. No unambiguous correlation could be,

Cord 2/3

ACC NR: AP7002735

established between these values and the fusibility diagrams of each system. The elucidation of the concentration dependence of the "effective" mobility of atoms on the basis of various physical characteristics of the alloys in binary alloys will be the subject of subsequent investigations. Orig. art. has: 2 tables, 4 figures, 3 formulas.

SUB CODE: 11, 20/ SUBM DATE: 04Apr66/ ORIG REF: 005/ OTH REF: 019

 $c_{-1} = 3/3$

AKULOV, V.D.; UGAY, L.P.

Diagnosis of congenital cysts of the lung in early childhood. Sov. zdrav. Kir. no.2:62-63 Mr-Ap '62. (MIRA 15:5)

l. Iz detskogo otdeleniya (ispolnyayushchiy obyazannosti zaveduyushchego - B.L.Kibrik) i patomorfologicheskoy laboratorii (zav. - kand.med.nauk S.Kh.Khamitov) Kirgizskogo nauchno-issledovatel skogo instituta tuberkuleza.

(LUNGS-TUMORS) (CYSTS)

PAK, Aleksey Andreyevich; ISAYENKO, N.P.; UGAY, M.A.

[Diversified state farms on virgin lands; based on the example of the "Kustanaiskii" State Farm, Kustanay Province] Mnogootraslevoi sovkhoz na tselinnykh zemliakh; na primere sovkhoza "Kustanaiskii," Kustanaiskoi oblasti. Moskva, Gos.izd-vo selikhoz.lit-ry, 1959.

(MIRA 12:12)

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no. 5, 1965, 663	1-667					
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ACCESSION NR: AP5016580

SUBMITTED: 19Jan65

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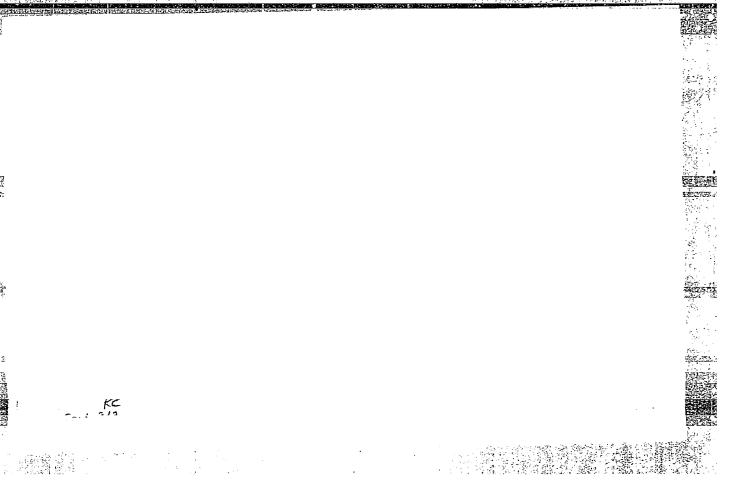
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Lityutakaya, L. A.

"APPROVED FOR RELEASE: 04/03/2001 CIA-RDP86-00513R001857820011-8

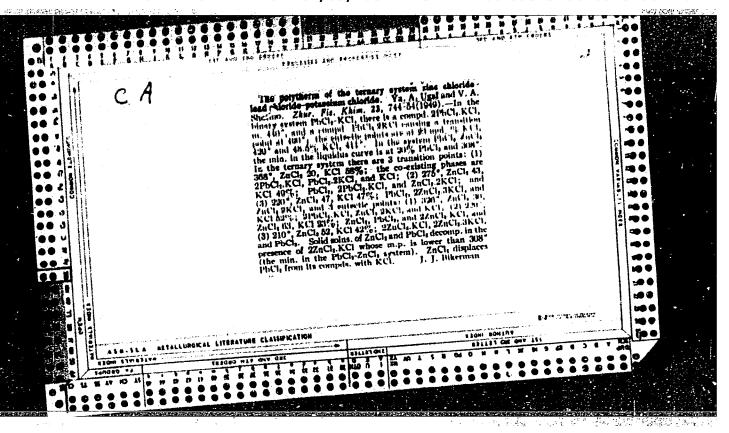
Card 1/3



UGAY, Ya.A.; ZAVALISKIY, Yu.P.; UGAY, V.A.; BOLKHOVITINA, N.B.

Production of indium phosphide by precipitation from a solution and some of its properties. Izv. AN SSSR. Neorg. mat. 1 nc.5:663-667 My '65. (MIRA 18:10)

1. Voronezhskiy gosudarstvennyy universitet.



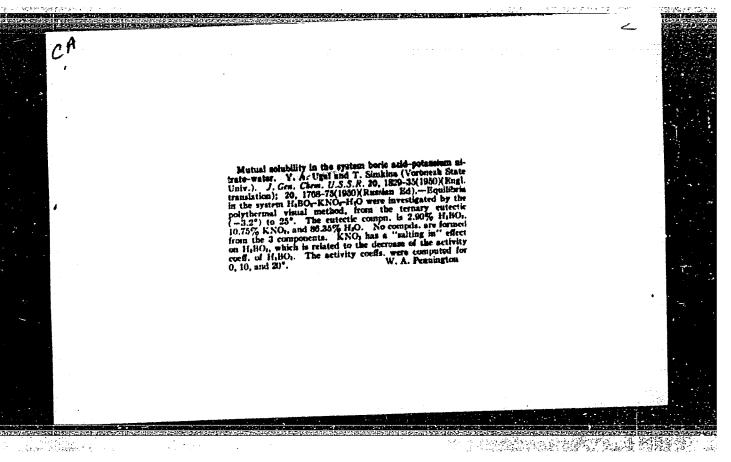
UGAI, YA. and

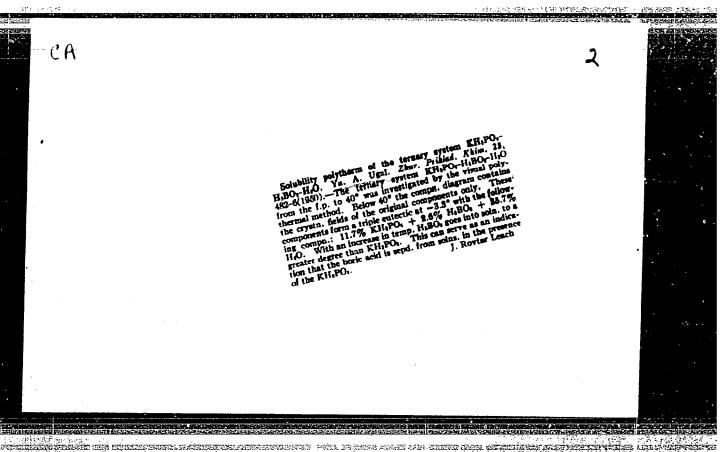
Ugai, Ya.; Simkina, T.

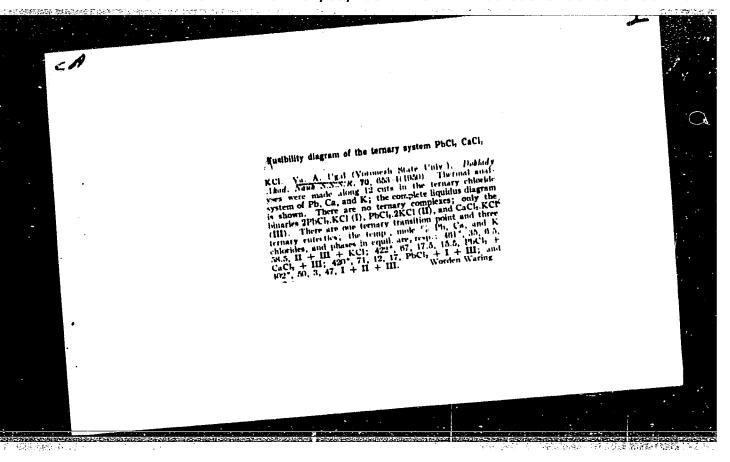
"Mutual Solubility in the System H_3BO_3 - KNO_3 - H_2O_{\bullet} " (p. 1768)

SO: Journal of General Chemistry, (Zhurnal Obshchei Khimii), 1950, Vol. 20, No. 10.

APPROVED FOR RELEASE: 04/03/2001 CIA-RDP86-00513R001857820011-8"







UGAY, Ya.A.; GORDIN, V.L.

Crowing of indium phosphide single crystals. Izv. AN SSSR.Neorg.
mat. 1 no.7:1051-1053 Jl '65. (MIRA 18:9)

1. Voronezhskiy gosudarstvennyy universitet.

THE PROPERTY OF THE PARTY.

UGAY, Ya.A.; BITYUTSKAYA, L.A.

Thermal stability of indium phosphide. Izv. AN SSSR. Neorg. mat. 1 no.7:1054-1056 Jl '65. (MFA 18:9)

1. Voronezhskiy gosudarstvennyy universitet.

URAY, Ye.A.; GOMONGROW, Ye.G.; BOLKHOWETTHA, N.E.; SHWYFEVA, W.H.

Preparation of solid solutions leave an observation along the length of the ingot. lev. AN COSR. Nearg. mat. 1 ma.71 1104-1108 J1 165.

1. Voronezhakiy gosudaratvennyy universitet.

UGAY, Ya.A.; AVERRAKH, Ya.M.; KHUGLOVA, G.S.

Production of single crystals of semiconductor phases in the system $Zn - Sb_{\bullet}$ Tay, when uchet, zay, fiz. 8 no.3:109-133 (65. (41.54.13:9)

1. Voronezhskiy gosudarstvennyy universitet.

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APPROVED FOR RELEASE: 04/03/2001 CIA-RDP86-00513R001857820011-8"

UGAY, Ya . A.

USSR/Chemistry Decomposition

Card : 1/1

Authors : Ugay, Ya. A.

Title : Thermographic investigation of the decomposition of exalates of divalent

metals

Periodical: Zhur. ob. khim. 24/8, 1315 - 1321, August 1954

Pub. 151 - 8/33

Abstract: The decomposition of Fe, Ni, Co, Mn, Cu, Zn, Cd, Hg, Sn, Pb, Mg, Ca, Sr, Ba-exalates as well as exalic acid, was investigated thermographically.

The endo- and exothermal type of curves showing the temperature of the thermal decomposition of exalates of bivalent metals, was established. Irreversible conversion of the unstable solid substance into a thermodynamically stable crystalline state, was observed in several instances.

The nature of the exalate decomposition and its effect on the form of the thermograms, are explained. Eight USSR references (1939 - 1953).

Tables; graphs.

Institution : State University, Voronezh

Submitted : February 22, 1954

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HOAY, YA.A.

USSE/Chemistry - Reaction processes

Card 1/1

Pub. 22 - 23/51

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Authors

• Ugay, Ya. A., and Baslyk, Yu. A.

Title

Chemical reaction of Ni with Zn

Periodical : Dok. AN SSSR 101/2, 281-283, Mar 11, 1955

Abstract

Experimental data are presented regarding the chemical reaction of components occurring during the heating of Ni and Zn powders. A change in volume particularly for compositions of greater Ni content was observed Charles the eighther to the Mi-On mixture. It was established than the Ni-Zn reaction has an explosive autocatalytic nature caused by the appearance of melted Zn in the mixture. Three references: 2 USSR and 1 German

(1935-1953). Graphs.

Institution: State University, Voronezh

Presented by: Academician G. G. Urazov, October 4, 1954

Ugay

USSE/Physical Chemistry - Thermodynamics, Thermochemistry, Equilibria,

Physical-Chemical Analysis, Phase Transitions.

B-8

Abs Jour: Referat. Zhurnal Khimiya, No 2, 1958, 3816.

Author : Ya. I. Ugay, A.P. Palkin

: Voronezh University. Inst

: Shift Regularity of Metathesis and Replacement Reactions Title

in Absence of Solvents.

Orig Pub: Tr. Voronezhsk. un-ta, 1956, 40, 11-16.

Abstract: The authors show with 30 examples that it is possible to judge

upon the metathesis direction by the difference between the total energies of crystal lattices of salts to the right and to the left of the equality sign in the reaction equation AX +

BY = AY + BX.

: 1/1 Card

-52-

USSR/Physical Chemistry, Thermodynamics, Thermochemistry, Equilibria, Physical-Chemical Analysis, Phase Transitions.

Abs Jour: Ref Zhur-Khimiya, No 5, 1957, 14614

Abstract: talline salt, the gaseous cation and the gaseous anion

taken from thermochemical tables. Calculations for Id, Mg, Ca, Sr, Ba, Al, Mn, Fe, Co and Ni chloride hydrates are carried out. It is found that the lattice energy decreases with the increase of the number of water mole-

cules in the crystal hydrate.

Card 2/2

SOV/137-58-8-17663

Investigation of the Quaternary Zn-Cd-Al System (cont.)

 $Zn_4^2Sb_3^*AlSb_i$ is obtained the eutectic point of which lies on the ordinate of the ZnSb compound. A true phase diagram of the $\angle nSb$ AlSb system exhibits a region of limited solid solutions of AlSb in $\angle nSb$.

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1. The inter-ontinony-order the sine systems in Typis

Card 2/2

"APPROVED FOR RELEASE: 04/03/2001

CIA-RDP86-00513R001857820011-8

78-3-3-23/47

A THOR 8

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Ugay, Ya. A.

TITLE:

On the Phase Diagrams in the System Sb-Zn in the State of Nonequilibrium (O diagramme sostoyaniya sistemy Sb-Zn v neravnovesnykh usloviyakh)

PERIODICAL:

Zhurnal Neorganicheskoy Khimii, 1958, Vol. 3, Nr. 3, pp.678-682 (USSR)

ABSTRACT:

The phase diagrams in the system Sb. In the nonequilibium state were examined. By the powder metallurgical and the casting method a complete agreement of the liquidus curve could be attained. Alloys with a 10, 20, 30, 32, 35, 38, 42, 43, 45, 50, 60, 70, 80, 90 and 99 % content of zinc were produced. On the action of antimony upon zinc ZnSb with 35 % zinc is the most important compound forming on that occasion. This compound has a partial peritectic melt at 547,50 c. The most complicated thermogram was produced for the compounds Zn₄Sb₂ and Zn₃Sb₂. In the system Sb. In the chemical interaction of the components in the nonequialibrium state can be concluded on the basis of the equialibrium state can be concluded on the basis of the equialibrium state can be concluded on the basis of the equialibrium state can be concluded on the basis of the equialibrium state can be concluded on the basis of the equialibrium state can be concluded on the basis of the equialibrium state can be concluded on the basis of the equialibrium state.

Card 1/2

78-3-3-23/47

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On the Phase Diagrams in the System Sb Zn in the State of Nonequilibrium

librium phase diagram. By the determination of electric conductivity and density in the system Sb-Zn follows that the compound ZnSb does not decompose during melting. There are 9 figure a and 9 references: which are Soviet.

ASSOCIATION: Vorone zhakiy gosudaratvenny universitet kafedra neorgani-

cheskoy khimii

(Voronezh State University, Chair for Inorgania Chemistry)

SUBMITTED: June 25, 1957

Card 2/2

UUAY, Ya.A.

Structural diagram Sb - Zn system in unbalanced state. Zhur. neorge (MIRA 11:4)
khim. no.3:678-682 '58.

1.Voronezhskiy gosudarstvennyy universitet kafedra neorganicheskoy khimii.

(Antimony-zinc alloys)

PALKIN, A.P., prof., otv. red.; ZAVGORODNIY, S.V., red.; OCHNEVA, O.S., red.; PEROVA, A.P., red.; UGAY, Ya.A., red.; SHATALOV, A.Ya., red.; SHATALOV, V.P., red.

可透透解析

[Transactions of the Voronezh Branch of the D.I.Mendeleev All-Union Chemical Society] Sbornik trudov Voronezhskogo otdeleniia Vsesoiuznogo khimicheskogo obshchestva imeni D.I.Mendeniia Vsesoiuznogo khimicheskogo obshchestva imeni D.I.Mendeleev All-niia Vsesoiuznogo khimicheskogo obshchestva imeni D.I.Mendeleev All-niia Vsesoiuznogo khimicheskogo obshchestva imeni D.I.Mendeniia Vsesoiuznogo khimicheskogo obshchestva imeni D.I.Mendeleeva imeni D.I.Mend

1. Vsesoyuznoye khimicheskoye obshchestvo imeni D.I.Mendeleyeva. Voronezhskoye otdeleniye.

APPROVED FOR RELEASE: 04/03/2001 CIA-RDP86-00513R001857820011-8"

UGAY, Ya.A.; VIGUTOVA, T.N.

New intermetallic semiconductor compounds. Fiz.tver.tela 1 (MIRA 13:5)

1. Voronezhekiy gosudarstvennyy universitet. (Semiconductors)

UGAY, YA.H.

82795

S/081/60/000/009/002/002 4003/4001

//. 8000 Translation from: Referativnyy zhurnal. Khimiya, 1960, No. 9, p. 65, # 34069

AUTHOR:

Ugay, Ya.A.

TITLE:

On the Problem of Heat Explosion in Some Solid-Phase Reactions

PERIODICAL:

Tr. Voronezhsk. un-ta, 1959, Vol. 57, pp. 23-29

TEXT: With the aid of Kurnakov's pyrometer with automatic heat regulation, the development of an exothermic reaction in mixtures of powder-like halides and pure metals was investigated. At a sufficiently high heating rate, the accelerating exothermic reaction changes into a heat explosion, e.g., in a CuCl+Zn mixture at 220°C, and in a mixture of FbCl₂+Zn at 278°C. Heat explosion arises also in mixtures of metal powders, if they are sufficiently finely ground, e.g., in a mixture of Fe and Al at 557°C. The development of an exothermic reaction in coarsely-grained material is damped and it is resumed again after melting of Al. The increased activity of newly-prepared powders of salts and metals is noted, which is ascribed to the formation on their surface of free valencies.

A. Sokolik

Translator's note: This is the full translation of the original Russian abstract.

Card 1/1

UGAY, Ya.A.; KOROTKOVA, Ye.I.

Interaction between copper and sinc under nonequilibrium conditions. Trudy VGU 57:31-37 '59. (MIRA 13:5) (Copper) (Zinc)

Asymmetry of Kel, 2 lines of zinc in its semiconductor compounds with antimony. Fiz. tver. tela 3 no.1:100-102 Ja '61.

(MIRA 14:3)

1. Voronezhskiy gosudarstvennyy universitet.

(Zinc antimonide)

<u>24.7700</u> 5.2610 24054 \$/020/61/138/004/015/023 B103/B203

AUTHORS:

Ugay, Ya. A., Dolgova, Yu. Ya., and Zyubina, T. A.

TITLE:

The intermetallic compound Cd₄Sb₃

PERIODICAL: Akademiya nauk SSSR. Doklady, v. 138, no. 4, 1961, 856-858

TEXT: Within the systematic study of semiconductor compounds, the authors studied the system Cd—Sb. In addition to the known compounds CdSb (stable) and Cd₃Sb₂ (metastable), they detected Cd₄Sb₃ (similar to Zn₄Sb₃) in the system Cd—Sb. They studied this system thermographically and by X-rays, and examined its microstructure and microhardness. They studied the electrical conductivity and the thermo-emf on cadmium alloys with a maximum of 5·10⁻³% impurities, and antimony of the type Cy 000 (Su000). KAO (KdO cadmium and Cy 00 (Su000) antimony were used for other determinations. Three series of alloys were heated to 650°C in evacuated (to 7·10⁻³ mm Hg) Pyrex ampuls, and shaken at 500-550°C for 5 hr. Series 1 was cooled in the air, series 2 together with the furnace, series 3 was annealed between 250 and 420°C for one week. Kurnakov's pyrometer of the type TK-55

X

Card 1/4

24054 \$/020/61/138/004/015/023 11103/13203

The intermetallic compound ...

(FPK-55) with an evacuated Stepanov vessel [Abstracter's note: Stepanov vessel not stated] was used for taking thermograms. Debye patterns were recorded with a standard camera. Fig. 1 shows the phase diagram of the system Cd—Sb on the basis of all results. The new compound Cd₄Sb₃ (44.9% by weight of Sb) is pointed out. It melts congruently at 460°C. Both the microhardness (180 kg/mm²) and the microstructure of Cd₄Sb₃ deviate from the values of known compounds. The microstructure indicates perfect homogeneity. In contrast to other compounds of the system Cd—Sb, Cd₄Sb₃ is formed under quick cooling. Its existence is confirmed by X-ray examination. Cd₄Sb₃ has a tetragonal lattice, probably of the rutile type, namely: a = 8.1, o = 13.0 Å, c/a = 1.6, whereas CdSb crystallizes in the rhombic, and Cd₃Sb₂ in the monoclinic system. Cd₄Sb₅ forms, in a pure state, silver-gray, brilliant, very brittle crystals with a fracture reminding of germanium. When heated in the air, they oxidize much less than other phases of the system Cd—Sb, and they have a specific conductivity of 20 ohm—1.cm¹ at room temperature. Their highest

Card 2/4

24054 \$/020/61/138/004/015/023 B103/B203

The intermetallic compound ...

thermo-emf observed was 420 µv/degree, which decreased strongly at high temperature. The temperature dependence of Cd₄Sb₃ shows typical semiconductor features. Dislocations of the spiral type are visible on the surface of Cd₄Sb₃ single crystals produced by Bridgman's method (V. D. Kuznetsov, Ref.4: Kristally i kristallizatsiya (Crystals and crystallization),1953,p.338). Cd₄Sb₃ crystals will become much larger when cooling is accelerated. Cd₄Sb₃ can dissolve excessive Sb amounts (up to 2% at room temperature). On a decrease in temperature, the excess is separated out again. Excess cadmium is practically of dissolved in Cd₄Sb₃. Both pure Cd₄Sb₃ and solid solutions of Sb in it are hole conductors. On the other hand, CdSb with excess Sb shows electron conductivity. There are 4 figures and 5 Soviet-bloc references.

ASSOCIATION:

Voronezhskiy gosudarstvennyy universitet (Voronezh State

University)

PRESENTED:

January 20, 1961, by I. I. Chernyayev, Academician

SUBMITTED:

January 15, 1961

Card 3/4

~/176<mark>/61/000/000/014/0</mark>20 ~475/E535

AUTHOR Ugay Ya ...

TITUE

On some new autimony-based semiconductor phases

SOURCE.

Soveshchaniye po poluprovodnikovym materialam Ath Voprosy metallurgit i fiziki poluprovodnikov, poluprovodnikovyye sovedineniya i tverdyye silavy frudy soveshchaniya Moscow, Izd-vo AN SSSR, 1901. Akademiya nauk SSSR Institut metallurgii imeni A A Baykova Fiziko-tekhnicheskiy institut, 107-109

The intermetallic compounds Li_3Sb. Na_Sb. NaSb were produced and some of their properties investigated. For producing these compounds ordinary methods of synthesis in evacuated ampoules are unsuitable. Therefore, the required quantities of the starting metals were charged into a steel crucible which was placed into a specially prepared eaction unit made of a refractory alloy. This unit was filled with dry inergas and then hermetically closed. Following that, it was heated in a furnace to the required temperature, maintained at that temperature for 30 min and then the furnace was switched off and Card 1/5.

On some new antimony-based.

\$/576/61/000/000/014/020 E073/E535

the unit was allowed to cool slowly in the closed furnace. initial materials sodium of 99.8% purity, lithium of 99.6% purity (with impurities of Mg Fe. Mn Al and others) and antimony with a total content of impurities of 2.1 x 10-3 % were used. The composition of the compounds was chemically analysed with a maximum error of 0.01%. The sodium compounds were additionally subjected to thermal analysis in a nitrogen atmosphere. A temperature vs time graph is given in Fig.1 for the compound No. Sb The unconendothermic nature of the fusion movess I gother with the results of chemical analysis, conformed to beence of a second phase this does on analy to enumerally . Na in compounds: the reproductible reports obtained by the . or showed a fusion compensatore for Na Sb which is somewhat he for than the value published by Matherson (Ref. 3. Z.anorg, us. allg Chem . 1906 A characteristic feature of all the compounds produced is 192) , was practically Therefore their ion stability in air · 千里:柳桂花园的诗堂家村长艺艺。 empossible to impositioned and photocies ans of a compensation the electric conductivity was measured was determined from th method and the sign of the current () The constitution of the arm retractions dependence w thermal e m f Card 2/5

s/576/61/000/000/014/020 E073/E435

On some new antimony-based ...

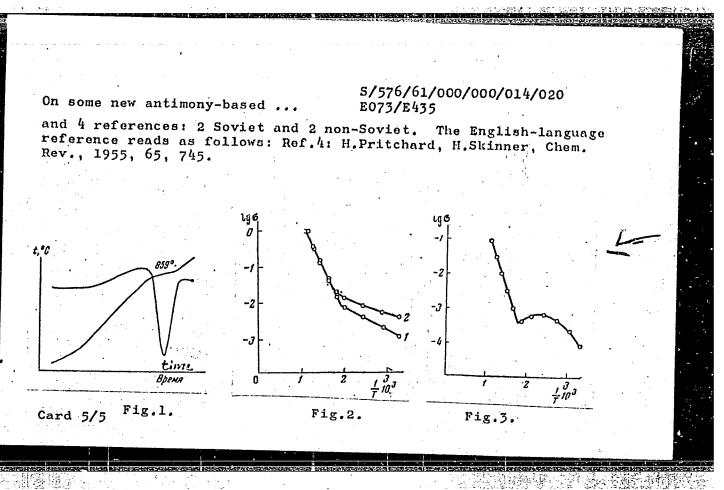
determined using a specially manufactured vacuum furnace in which a vacuo of 5 x 10^{-2} mm Hg was maintained during the measurements. Under these conditions the specimens did not oxidize and did not become decomposed by water vapour. Fig.2 shows the temperature dependence of the conductivity of Li3Sb with varying deviations from the stoichiometric composition (curve 1 - excess Sb 0.01%, curve 2 - excess Sb 0.6%). In spite of the appreciable deviations from stoichiometry, no metallic conductivity was observed in the range of mixed conduction. Thus, Li3Sb and Na3Sb do not show semimetallic properties, in contrast to those intermetallic semiconductors like ZnSb and CdSb. The lg o versus 1/T curve does not show any region of depletion of the impurity current carriers, whilst the analogous curve for Na3Sb (Fig. 3) shows clearly such a region. The following table contains data on the compounds investigated.

Card 3/5

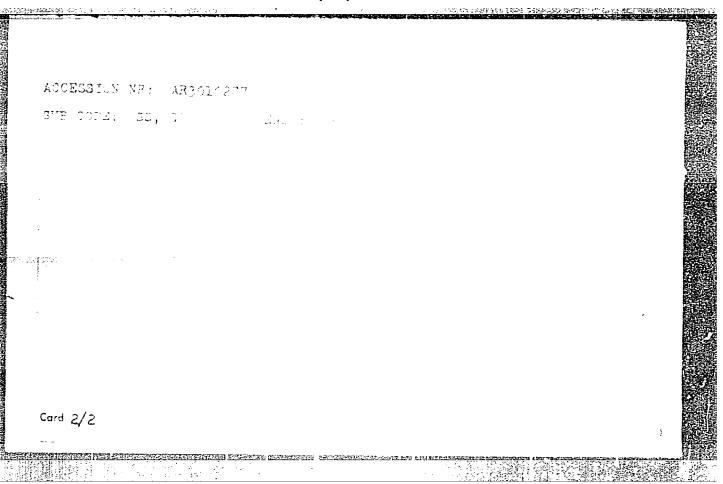
S/576/61/000/000/014/020 E073/E435

Cn some new Substance	Colour	T _{fus} ,	o,m ⁻¹ cm ⁻¹ at 20°C	E _o ,eV	Conduct- ivity	
	Light grey		1.8 x 10-4	1.25	p-type	
Li ₃ Sb	Bluish grey		9.5 x 10 ⁻⁵	1.52	11	
Na 38b Na Sb	Silvery white	465	2.1	0.82	II	

The width of the forbidden zone of the NaSb is 0.82 eV, which is slightly smaller than for KSb. This is explained by the fact that KSb is more ionic than NaSb since the electronegativity of potassium is less than that of sodium. The p-type conductivity of all the specimens investigated is attributed to the following two causes: 1) In compounds with a high fraction of ionic bonds the admixture atoms which fulfil the function of a non-metal always form acceptor levels. In the compounds investigated, antimony plays the role of an anion forming element. 2) Spontaneous crystallization without subsequent annealing leads to numerous lattice defects which usually act as acceptors. The students T.N.Vigutova, V.Z.Anokhin and O.Ya.Gukov participated in the experimental part of the work. There are 3 figures, 1 table Card 4/5



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24,7700

<u>36ኒ69</u> s/181/62/004/003/007/045 B102/B104

AUTHORS:

TITLE:

Ugay, Ya. A., Averbakh, Ye. M., Marshakova, T. A., and Matvey-

.

Some electrical properties of the intermetallic semiconducting compound Cd_4Sb_3 doped by various impurities

PERIODICAL: Fizika tverdogo tela, v. 4, no. 3, 1962, 615 - 617

TEXT: In order to determine the effect of Ag, Cd, In, Sn, Pb, Sb, and Te impurities in quantities of up to 1 at% an Cd₄Sb₃, the temperature dependence of conductivity in the range 20 - 300 °C, the Hall constant, and the thermo-emf at room temperature were measured. d - c measurements were made with a two-probe compensation method; the thermo-emf was determined with respect to copper; the field strength in the slit of the electromagnet was 2500 oe. Cd₄Sb₃ (impurity concentration 2.1·10-3%) was fused together with the doping metals (purity 99.996%) in evacuated quartz ampouls. The conduction type of the stoichiometric Cd₄Sb₃ (p-type) was changed only by Te impurities. Card 1/3

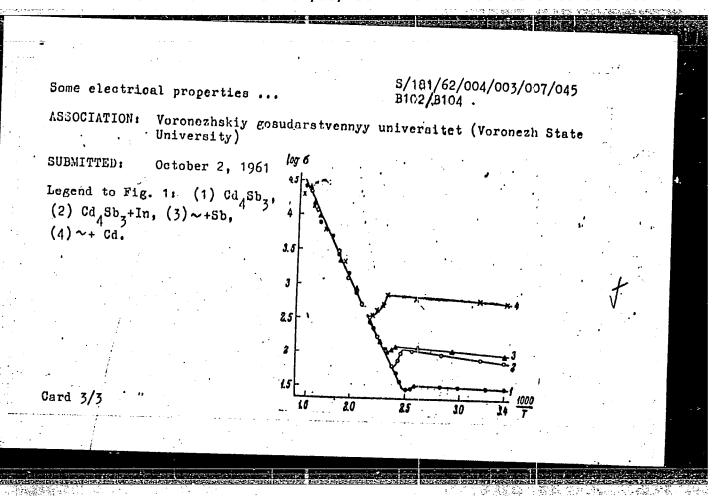
3/181/62/004/003/007/045 B102/B104

Some electrical properties ...

Composition	Thermo-emf	Conductivity (ohm·cm)-1	cm ² /v.sec
Cd ₄ Sb ₃	+100	30	900
with Ag with In with Te	+47 +130 +29 or -77	4000 80 2900 or 5100	800 45 345 or 1035

The forbidden band width as determined from the log oversus (1/T) curve was 1.25 ev. Cd₄Sb₅ of stoichiometric composition has a carrier concentration of 2.10·10 decay. Sb additions increase this value up to 10¹⁶ cm⁻³, the other metals even up to 10¹⁹ cm⁻³. The Cd-Sb alloy consists of CdSb and Cd₄Sb₅. The stoichiometric and the Te-doped samples (p-type) show rectifying properties; the Te-doped samples also show a range of negative resistivity in the back direction. If the current is raised to more than 4 ma the rectifying effect vanishes. There are 2 figures, 1 table, and 5 Soviet references.

Card 2/3



APPROVED FOR RELEASE: 04/03/2001 CIA-RDP86-00513R001857820011-8"

l₄3130 **S/181/62/004/011/031/049** B125/B186

24.7700

AUTHORS: Ugay, Ya. A., Averbakh, Ye. M., and Lavrov, V. V.

TITLE: Certain electric properties of the intermetallic compound

β-Zn₄Sb₃

PERIODICAL: Fizika tverdogo tela, v. 4, no. 11, 1962, 3270-3272

TEXT: In order to reveal semiconducting properties in stoichiometric $2n_4Sb_3$ the temperature dependences of the electric conductivity and of the thermo-emf, of single and polycrystals were measured in the range 20-400°C. The Hall constant was measured at room temperature. A stoichiometric melt of Zn and Sb was kept slightly above the melting point of $2n_4Sb_2$ and was continuously mixed by vibration. Small crystals of β -modification were

continuously mixed by vibration. Small crystals of \(\beta\)-modification were prepared by quenching the melt in ice-water. The coarsely crystalline specimens were produced by slowly cooling. Single crystals were obtained by zone melting of the coarsely crystalline specimens. At room temperature all samples showed hole-type conductivity. Results: \(\begin{align*}
2n_4 \begin{align*}
2b_3 \end{align*}
2n_4 \begin{align*}
2b_4 \end{align*}
2b_4 \

by zone melting. β -Zn₄Sb₃ is a semiconductor with a width of the forbidden

Card 1/3

Certain electric properties of ...

5/181/62/004/011/031/049

band of 1.20 ev. The clear metallic conductivity of the β sample A7 (Fig. 1) is attributed to additional acceptors formed as a result of lattice defects in quenching. There are 2 figures and 1 table.

ASSOCIATION: Voronezhskiy gosudarstvennyy universitet (Voronezh State

University)

SUBMITTED: June 29, 1962

Fig. 1. logo versus inverse temperature. Legend: B5 - single crystal, 612 - coarsely crystalline, A7 - β -modification.

Fig. 2. Differential thermo-e.m.f. ($\mu\nu/deg$) versus inverse temperature.

Card 2/3

S/078/62/007/003/019/019 B110/B138

Production and investigation...

chloric acid solution of SbCl, introduced into the lower end of the column produced: SbCl3 + 3HCl3 + 3Mg = 3MgCl2 + SbH3 . SbH3 was dried with CaCl₂ and reacted as follows: 3HgCl₂ + 2SbH₃ = Hg₃Sb₂ + 6HC1T. The reaction took 2 - 3 hrs. The specific gravity of the powdery heavy gray Hg 3Sb 2, determined pyknometrically, was 6.0 g/cm3. When heated in air Hg 3Sb 2 decomposes to mercury and antimony oxides around 400°C, and if heated in vacuum, into its elements at above 450°C. It is practically insoluble in water, alkali, and hydrochloric acid, partly soluble in concentrated HNO3, and highly soluble in boiling H_2SO_4 and aqua regia. When left in air it moistens after 2-3 weeks and Hg drops separate. electrical resistivity, by the compensation method and a MNTB-1 (PPTV-1) potentiometer measured on a tablet pressed from the powder (250 kg/cm²), was 1012 ohms cm. In cast Hg 35b at room temperature conductivity is ~10-11 ohm-1.cm-1. The sign of the thermo-e.m.f. points to hole conductivity. The logarithmic temperature dependence, log $\sigma = f(10^3/T)$, of specific conductivity at $7 \cdot 10^{-3}$ mm Hg shows that dissociation begins at Card 2/3

Production and investigation ...

S/078/62/007/003/019/019 B110/B138

370°C (3.8 ± 0.2 ev). As the valence and conduction bands are farapart, Hg₃Sb₂ is close to the dielectrics, Good absorption properties prove the nonmetallic character of its chemical bond. There are 2 figures and 9 references: 7 Soviet and 2 non-Soviet. The reference to the English-language publication reads as follows: Mellor's Comprehensive Treatise on Inorganic and Theoretical Chemistry, 9, p. 391, 1947.

ASSOCIATION: Voronezhskiy gosudarstvennyy universitet (Voronezh State University)

SUBMITTED: September 28, 1960

Card 3/3

3 . 194

s/078/62/007/004/014/016 B107/B101

94177

AUTHORS:

Ya. A., Kotosonov, N. V., Fogel'son, R. L., Tkacheva,

Some properties of Ca3Sb2 prepared by the method of S. A. TITLE:

Vekshinskiy

Zhurnal neorganicheskoy khimii, v. 7, no. 4, 1962, 930 - 931 PERIODICAL:

TEXT: The present paper describes the preparation of a thin film (5 - 20μ) of Ca3Sb2. The temperature dependence of the specific conductivity was measured (Fig. 2). The compound Ca3Sb2 has hitherto not been synthesized, and has only been mentioned by M. Hansen (see below). It was obtained by simultaneous evaporation of Ca and Sb in a vacuum of 10^{-5} mm Hg (method of S. A. Vekshinskiy; Novyy metod metallograficheskogo analiza splavov (A new method of metallographic analysis of alloys), Gostekhizdat, 1944). The vapor was collected by mica foils previously heated to 300°C. The resulting film transmits a narrow stripe of orange-colored light, corresponding to Ca, Sb2. The compound can be left in air for a long time. Card 1/32

S/078/62/007/004/014/016 B107/B101

Some properties of Ca₃Sb₂...

The resistance was measured with electrodes deposited on the foils by the evaporation of antimony. Preliminary experiments had shown that the resistance of antimony was negligible. The resistivity of calcium antimonide at room temperature is 104 ohm·cm. The measurements are well reproducible. The distance between the valency band and the conduction band was calculated to be 1.4 ± 0.1 ev. Calcium antimonide is a slightly photoconductive compound. Its photoconductivity is increased by an oxide film which forms when the system is left without further evacuation. There are 2 figures and 7 references: 6 Soviet and 1 non-Soviet. The reference to the English-language publication reads as follows: M. Hansen. Constitution of Binary Alloys. New York, 1958.

ASSOCIATION: Voronezhskiy gosudarstvennyy universitet (Voronezh State

University)

SUBMITTED: February 20, 1961

Fig. 2. Specific conductivity of Ca3Sb2 as a function of temperature.

Card 2/3

\$/275/63/000/002/009/032 D405/D301

AUTHOR:

Ugay, Ya.A.

TITLE:

Physicochemical analysis and chemistry of scmicon-

ductors

PERIODICAL:

Referativnyy zhurnal, Elektronika i eye primeneniye, no. 2, 1963, 2, abstract 2310 (Fiz.-khim. analiz solevýkh sistem, Rostov-na-Donu, Rostovsk. un-t,

1962, 201-212 (Collection))

The main problems of semiconductor chemistry are formulated: the search for new semiconductor materials of given tormilated: the search for new semiconductor materials of given properties; ascertaining the nature of the chemical bond in semi-conductors; studying the dependence of the electrical and physico-chemical properties on the composition; the development of methods chemical properties on the composition; the development of methods for obtaining semiconductors of high purity [Abstracter's note: for obtaining semiconductors of high purity [Abstracter's note: a missian text the word "chastota" appears, which is obviously a misprint for "chistota" [Abstracter is note: a misprint for "chisto

Card. 1/2

Physicochemical analysis ...

S/275/63/000/002/009/032 D405/D301

of the properties of thin-layer semiconductors. Nothods of solution of these problems with the help of physicochemical analysis are discussed, and examples are given of scientific research work carried out in this direction on various semiconductor materials. 75 refer-

Card 2/2

Investigation of semiconducting phases based on antimony. Ya. A. Ugay.

Semiconducting phases in the system zinc-antimony. Ya. A. Ugay, Ye. M. Averbakh.

[Study and some properties of thin layers of inclum phosphide. Ya. Ugay, R. L. Fogel'son, V. V. Lavrov. (Not presented).]

Report presented at the 3rd National Conference on Semiconductor Compounds, Kishinev, 16-21 Sept 1963

AID Nr. 979-7

29 May

CHEMICAL BOND IN SEMICONDUCTING COMPOUNDS OF Z_n AND Sb (USSR)

Ugay, Ya. A., Ye. P. Domashevskaya, and T. A. Marshakova. Zhurnal strukturnoy khimii, v. 4, no. 2, Mar 1963, 250-253. S/192/63/004/002/001/002

per unit of "formal" valency, that is, the ratio of the total number of valence

Short-range interatomic order in the semiconducting compounds Zn₃Sb₂, ZnSb, and Zn₄Sb₃ has been studied by x-ray spectroscopy at the Voronezh State University. The $K\alpha_1$ and $K\alpha_2$ lines of Zn in all three compounds were observed to shift toward the short-wavelength region as compared with the same lines in $Z_{\rm n}$ metal. The shift, which increased in the order $Z_{\rm n_3Sb_2} < Z_{\rm nSb} < Z_{\rm n_4Sb_3}$, is attributed partly to an assymetric distribution of density in the electron cloud. This distribution is responsible for a decrease in the shielding effect of the Valence electrons and, thus, for an increase in the effective charge of the cationic nucleus. The shift is ascribed in part also to the difference in valency of the cationic element in each compound. The shift of the $K\alpha_1$ and $K\alpha_2$ lines

Card 1/2

AID Nr. 979-7 29 May

CHEMICAL BOND [Cont'd]

5/192/63/004/002/001/002

electrons in Sb to the number of Z_n atoms in the compound, was shown to increase in the order $Z_nS_b < Z_{n_3}S_{b_2} < Z_{n_4}S_{b_3}$. The contribution of the ionic bond increases in the same order and is correlated with the semiconducting properand $C_{a_3}S_{b_3}$; that is, the widths of the forbidden zone in these semiconductors increase in the same order as the ionic-bond contribution.

Card 2/2

"APPROVED FOR RELEASE: 04/03/2001 CIA

CIA-RDP86-00513R001857820011-8

L 11116-63 SWF(q)/EWT(F)/EDS AFFTC/ASD JD

ACCESSION NR: AP3000602 JD

AUTHOR: Ugay, Ya. A.; Averbakh, Ye. M.

5/0181/63/005/005/1291/1292

55

TITLE: Some electrical properties of intermetallic e-Zn, Sb₂ SOURCE: Fizika tverdogo tela, v. 5, no. 5, 1963, 1291 1292

TOPIC TAGS: zinc antimonide electrical property, zinc antimonide electroconductivity, zinc antimonide differential thermal emf

ABSTRACT: Measurements of temperature dependence of electroconductivity and differential thermal emf in the interval of 20 to 4700 were carried out on five polycrystalline specimens of ε -Zn₃ Sb₂ of stoichiometric composition obtained by slow-cooling the melt. It was established that the low temperature ε -phase of Zn₃ Sb₂ is a hole-type semiconductor with a 0.2-ev width of the forbidden zone. The hole concentration of 6.6 x 10¹⁶ cm⁻³ and mobility of 200 cm²/v x sec were determined from the measurements of the Hall effect at room temperature and emf observed at 405 and 4370 can be explained by phase transitions of the intermal metallic Zn₃Sb₂ compound. Orig. art. has: 1 figure.

Card 1/2/

Voronezh St. University

UGAY, Ya.A.; MARSHAKOVA, T.A.; GONCHAROV, Ye.G. Effect of the nature of the chemical bond on the solubility of inorganic substances in the solid state. Zhur.neorg.klim. 8 no.1:177-185 Ja 163. (Chemical bonds)

(Solutions, Solid)

日 1990年12月1日 1990年11日 1990年11

CIA-RDP86-00513R001857820011-8 "APPROVED FOR RELEASE: 04/03/2001

<u>L 16976-63</u> Pzalı JD/AT

ENT(1)/ENG(k)/ENP(q)/ENT(m)/BDS AFFTC/ASD/ESD-3/IJP(C) \$/020/63/149/006/023/027

AUTHOR:

Ugay, Ya. A., Averbakh, Ye. M., Gukova, Yu. Ya., and Lavrov, V. V. Marketini da de la compania del compania del compania de la compania del compania del compania de la compania del compania de

TITLE:

A new semiconductor phase in zinc-antimony system

PERIODICAL:

Akademiya nauk SSSR. Dokledy. v. 149, no. 6, 1963, 1387-1389

TEXT: The authors investigated the intermetallic compound Zn_{li}Sb₃ in the Zn-Sb system, suspecting this compound to be a semiconductor. To prove this, they chose the beta-modification of Zn₄Sb₃, stably existing between -10 and 485°C. They isolated for the first time monocrystals of this compound by three different techniques and found it to be a gray substance with a metallic luster, fairly brittle, with a slightly vitreous, conchoidal fracture. Microhardness approximately 200 kg/mm2. The pycnometric specific weight of large crystals is 6.81. The possibility of cleaning this compound by zone recrystallization was demonstrated. The physicochemical and electrical properties of ZnuSb3 also are described here for the first time. There

ASSOCIATION: Voronezhskiy gosudarstvennyy universitet (Voronezh State University)

SUBMITTED: August 3, 1962

Card 1/1

ACCESSION NR: APLO11728

S/0181/64/006/001/0003/0006

AUTHORS: Ugay, Ya. A.; Khukhryanskiy, Yu. P.

TITLE: Determining the solubility of gallium in solid germanium by saturation currents of a p n junction

SOURCE: Fizika tverdogo tela, v. 6, no. 1, 1964, 3-6

TOPIC TAGS: gallium solubility, solubility, germanium, saturation current, p n junction, etching, Perhydrol, indium

ABSTRACT: By measuring the saturation currents of alloyed jurctions, the authors have determined the solubility of Ga in solid Ge during crystallization in the system Ge-In-Ga (with low Ga content). The studies were made in the temperature interval 360-550C. The concentration of Ga in the Ge was determined by measuring the saturation current of the p-n junction of samples in which the p-zone consisted of a recrystallized layer of Ge. This layer was formed by fusion of In platelets (with Ga addition) to n-type Ge. Etching was done with Perhydrol to which NaOH had been added, and the depth of etching was 0.19 mm. The concentration of Ga in

Card 1/32

ACCESSION NR: AP4011728

Ge is shown graphically in Fig. 1 on the Enclosure (in comparison with data from other authors). Some deviation is apparent, but the authors conclude that if the experimental curve is extrapolated to a temperature of about 6000 (as shown by the dashed lines in Fig. 1) the results will agree with data from the literature. It is concluded that in the interval tested In decreases the solubility of Ga in Ge. Orig. art. has: 4 figures and 4 formulas.

ASSOCIATION: Voronezhskiy gosudarstvenny*y universitet (Voronezh State University)

SUBMITTED: 17May63

DATE ACQ: 14Feb64

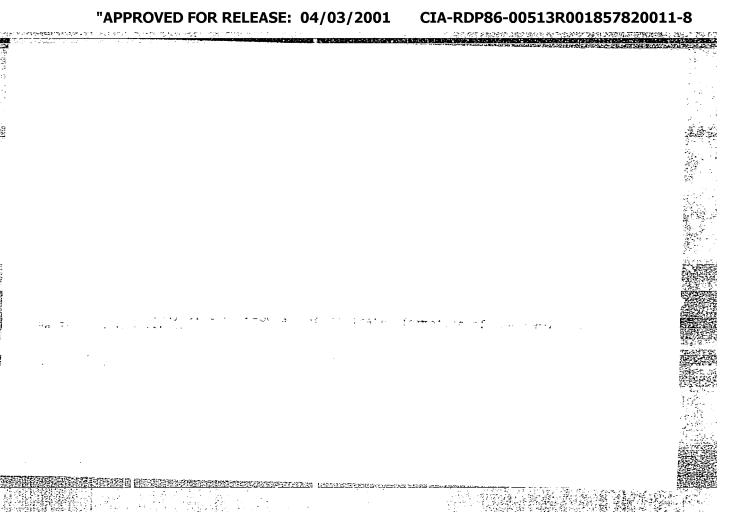
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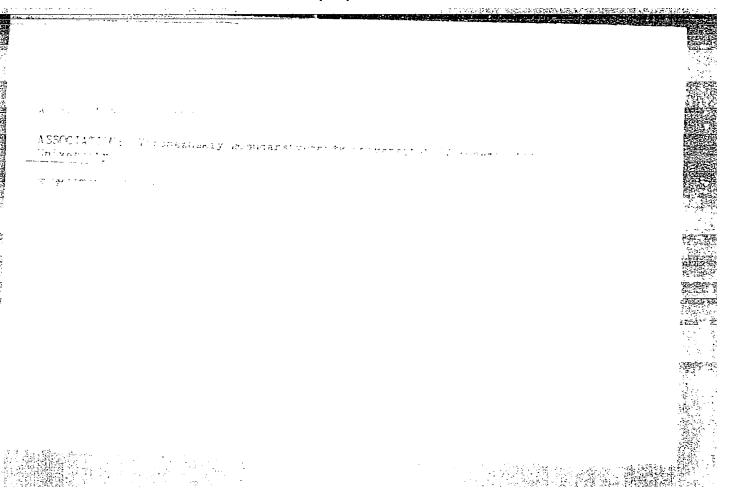
SUB CODE: PH

NO REF SOV: 004

OTHER: 005

Card 2/\$2





DOMASHEVSKAYA, E.P.; UGAY, Ya.A.

Lg2 15-emission spectra of cadmium and antimony in certain semiconducting compounds. Izv. AN SSSR.Ser. fiz. 28 no. 5: 853-856 My '64. (MIRA 17:6)

1. Voronezhskiy gosudarstvennyy universitet.

APPROVED FOR RELEASE: 04/03/2001 CIA-RDP86-00513R001857820011-8"

1. 语词的 \$克克斯巴巴尔基门 **建装**数

UGAY, Ya.A.; AVERBAKH, Ye.M.; FOGEL'SON, R.L.; GOL'DFARB, V.A.

Some properties of thin films of indium phosphide. Izv. AN
SSSR. Ser. fiz. 28 no.6:998-999 Je '64. (MIRA 17:7)

1. Voronezhskiy gosudarstvennyy universitet.

S/0048/64/028/005/0853/0856

AUTHOR: Domashevskaya, E.P.; Ugay, Ya.A.

TITLE: $1\beta_2$,15 emission spectra of cadmium and antimony in some semiconducting compounds Report, Seventh Conference on X-Ray Spectroscopy held in Yerevan 23 Sep to

SOURCE: AN SSSR. Izvestiya, Seriya fizicheskaya, v.28, no.5, 1964, 853-856

TOPIC TAGS: x-ray spectrum, x-ray emission, cadmium, cadmium compound, antimony, antimony compound, semiconducting material, chemical bond

ABSTRACT: The IB2,15 emission spectra of cadmium and antimony were recorded for the metals and for a number of compounds in order to determine the effect on them of different types of chemical bonding. The cadmium spectra were recorded for CdSb, Cd/Sb3 and CdS; the antimony spectra were recorded for CdSb, Cd4Sb3, AlSb, GaSb, InSb, Sb2Se3 and Sb2S3. A spectrograph with Johann focusing was employed. The cadmium spectra were recorded with a dispersion of 18.7 dV/mm in the first order reflection from the (111) planes of a bent (50 cm radius) silicon crystal; the antimony spectra were recorded with a dispersion of 6.1 eV/mm in the first order reflec-

Card 1/3

tion from the (0001) planes of a quartz crystal. The spectra are very similar, showing the IB2 and IB15 spin doublets and weak short wavelength structure of unknown origin. The Sb spectra are the more symmetric, the Cd spectra being considerably extended in the short wavelength direction. The simplest spectra are those of the metals, which show only a single unresolved spin doublet. The spectrum of the nearly covalent compound InSb is very similar to that of the metal, as is also the spectrum of GaSb. The compounds CdSb, Cd4Sb3, CdS, AlSb, Sb2Se3 and Sb2S3 are semiconductors with mixed ionic-covalent bonds. Both the Cd and Sb spectra of these compounds show both the spin doublets, and these are displaced with respect to each other. The separation of the spin doublet in the semiconducting compounds indicates the presence of two energy states of the Cd or Sb atom corresponding to the mixed ionic-covalent character of the bond. This separation is small in CdSb, indicating the predominately covalent character of this compound. The maximum of the Cd spectra is shifted toward the shorter wavelengths in the compounds compared with its position in the metal. This is ascribed to participation of Cd 4f electrons, along with the 5s valence electrons, in the chemical bonding. A similar phenomenon is mentioned in connection with the Sb spectra, but it is less convincingly revealed by the curves presented. Orig.art.has: 2 figures and 2 tables.

Card 2/3

ACCESSION NR: AP4038777

ASSOCIATION: Voronezhskiy gosudarstvenny*y universitet (Voronezh State University)

SUBMITTED: 00

DATE ACQ: 12Jun64

ENCL: 00

SUB CODE: OP

NR REF SOV: 013

OTHER: 007

Card 3/3

S/0048/64/028/006/0998/0999

AUTHOR: Ugay, Ys. A.; Averbakh, Ye. H.; Fogel'son, R. L.;

TITLE: Some properties of thin indium phosphide layers

SOURCE: AN SSSR. Izvestiya. Seriya fizicheskaya, v. 28, no. 6,

TOPIC TAGS: indium, indium phosphide, indium phosphide film, indium phosphide property, film property, film electric conductivity

ABSTRACT: The temperature dependence of electric conductivity of indium phosphide twin films and of their limit of absorption in the longwave range have been investigated. Films were produced by a separate vacuum vapor deposition of components, first of indium and then of phosphorus, under pressure of about 10-5 mm Hg at 400C. Electron diffraction patterns of the films corresponded to those of the InP compound. The temperature dependence of electric conductivity of input films 0.55-0.06 p thick was determined at 20-500C. One of cord

for 3 hr. As shown in the diagram (see Fig. 1 of the Enclosure), the electric conductivity of the films at high temperature is almost dentical. The width of the forbidden zone determined from this he longwave absorption edge was 1.27 ev. The higher value obtained rom the temperature dependence of electric conductivity is explained y partial decomposition of indium phosphide at high temperatures. SSOCIATION: Voronezhskiy gosudarstveny*y universitet UBMITTED: 00 ATD PRESS: 3058 ENCL: 01	y partial decomposition of indium phosphide at high temperatures. SSOCIATION: Voronezhskiy gosudarstveny*y universitet Voronezh State University) UBMITTED: 00 ATD PRESS: 3058 ENCL: 01			
for 3 hr. As shown in the diagram (see Fig. 1 of the Enclosure), the electric conductivity of the films at high temperature is almost dentical. The width of the forbidden zone determined from this he longwave absorption edge was 1.27 ev. The higher value obtained rom the temperature dependence of electric conductivity is explained y partial decomposition of indium phosphide at high temperatures. SSOCIATION: Voronezhskiy gosudarstveny*y universitet UEMITTED: 00 ATD PRESS: 3058 ENCL: 01	for 3 hr. As shown in the diagram (see Fig. 1 of the Enclosure), the electric conductivity of the films at high temperature is almost dentical. The width of the forbidden zone determined from this he longwave absorption edge was 1.27 ev. The higher value obtained from the temperature dependence of electric conductivity is explained by partial decomposition of indium phosphide at high temperatures. SSOCIATION: Voronexhskiy gosudarstveny*y universitet UBMITTED: 00 ATD PRESS: 3058 ENCL: 01	ACCESSION NR: AP4041363		man and a fee a sequence of the second and the seco
SSOCIATION: Voronezhskiy gosudarstveny*y universitet Voronezh State University) UBMITTED: 00 ATD PRESS: 3058 ENCL: 01	SSOCIATION: Voronezhskiy gosudarstveny*y universitet Voronezh State University) UBMITTED: 00 ATD PRESS: 3058 ENCL: 01	dentical. The width of lagram is 1.42 ev. The wine longwave absorption e	the forbidden zone det idth of the forbidden dge was 1.27 ev. The	ermined from this zone determined from higher value observations
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ACCESSION NR: AP4041373

8/0048/64/028/006/1044/1047

AUTHOR: Ugay, Ya.A.; Averbakh, Ye.M.

TITLE: Some electric properties of single crystals of ZnSb-CdSb solid solutions Report, Third Conference on Semiconductor Compounds held in Kishinev 16-21 Sep 183

SOURCE: AN'SSSR. Izvestiya. Seriya fizicheskaya, v.28, no.6, 1964, 1044-1047

TOPIC TAGS: semiconductor, solid solution, zinc antimonide, cadmium inorganic compound, electric conductivity, thermal emf, temperature dependence, Hall constant

ABSTRACT: The electric conductivity, Hall constant and thermal emf of single crystals of ZnSb-CdSb solid solutions were measured at temperatures from 20 to 220°C. The measurements were undertaken because of the low thermal conductivities and high form solid solutions in all proportions. Single crystals of the solid solutions were obtained by the zone leveling method. The crystals of the solid solutions, as well as those of the pure compounds, had two unequally marked cleavage planes. The samples were oriented for measurement with the less marked cleavage plane parallel to the current and perpendicular to the magnetic field. All the materials proved to

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be.p-type semiconductors. The thermal emf was found to be positive for all the sm ples over the full temperature range investigated. This is regarded as an indication that the hole mobility exceeds the electron mobility in the intrinsic conduction region, i.e., that the materials are anomalous semiconductors. The Hall mobilities were found to be proportional to T^{-n} (T is the absolute temperature) with n between 1.7 and 2.0. The value of n for the pure compounds is 1.66. The difference is ascribed to the greater concentration of lattice defects in the solid solutions. In about half the samples the value of n increased suddenly by a large factor (about 4) at some temperature within the range investigated and remained large at higher temperatures. This behavior is not understood. The energy gap, as determined from the temperature dependence of the conductivity, was 0.41 eV in both pure compounds and was less in the solutions. The minimum energy gap was 0.21 eV and occurred at a composition of 64 mole percent CdSb. The energy gap determined from the temperature dependence of the Hall constant was approximately 20% greater than that determined from the conductivity. This discrepancy is ascribed to the fact that not only the energy gap, but also the formation of lattice defects, contributes to the temperature dependence of the Hall constnat. Orig.art.has: 2 formulas, 4 figures and 1

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ACCESSION NR: AP4041373 ASSOCIATION: Voronezhskiy gosudarstvenny*y universitet (Voronezh State University) SUBMITTED: OO ENCL: OO SUB CODE: SS,IC NR REF SOV: OO7 OTHER: OOS Card 3/3								-		-				
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S/0020/64/156/002/0430/0433

AUTHOR: Ugay, Ya.A.; Domashevskaya, E.P.

TITLE: The nature of the chemical bond in AIII BV semiconductor compounds

SOURCE: AN SSSR. Doklady*, v. 156, no. 2, 1964, 430-433

TOPIC TAGS: semiconductor, III-V semiconductor, chemical bond, chemical bond type, energy position, L band, antimony, AlSb, GaSb, InSb, CdSb, x ray analysis, electron cloud contraction, binary compound,

ABSTRACT: The shape and the energy positions of the Last, 2-bands of antimony in antimony metal and its semiconductor compounds AlSb, GaSb, InSb and CdSb were examined by x-ray analysis to determine the behavior of the valency electrons responsible for the chemical bond. The emission spectra (fig. 1.) consist of two functions Ny—LIII and NIV—LIII. The shift in the Lettron transitions Ny—LIII and NIV—LIII. The shift in the Lettron toward the long wave (smaller energy) in AlSb, GaSb and CdSb is caused by Cord 1/5

of the indicated compounds; as the effective charge of the nucleus decreases, the L_{815,2} band shifts toward the long wave side. No shift is observed in the L_{815,2} spectra of InSb, and resolution of the L_{815,2} band is practically absent because of the covalent character of the interatomic bond. InSb is the most covalent (and least ionic) compound in the series as evidenced by the exceptionally high electron mobility and small width of the forbidden zone. The decrease in the width of the band in going from AlSb to InSb (from 12.8 to 9.8 e.v.) also indicates an increase in the degree of covalency, with the electronegativity increasing from Al to In. A new arrangement for AlII B compounds was drawn (see Fig.2) which fulfills the conditions for forming binary AB compounds with tetraheural coordination of the atoms in the compound. There is an average of four valence electrons per atom. The shift in the Sb spectrum toward the direction of less energy, due to the electron cloud contraction toward Sb, results in Al lattice sites with it and sb sites with it charges, where is much less than 1. Orig. art. has: 4 figures and 1 table.

ASSOCIATION: Voronezhskiy gosudarstvenny*y universitet (Voronezh State University)

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ACCESSION NR: AP4036727

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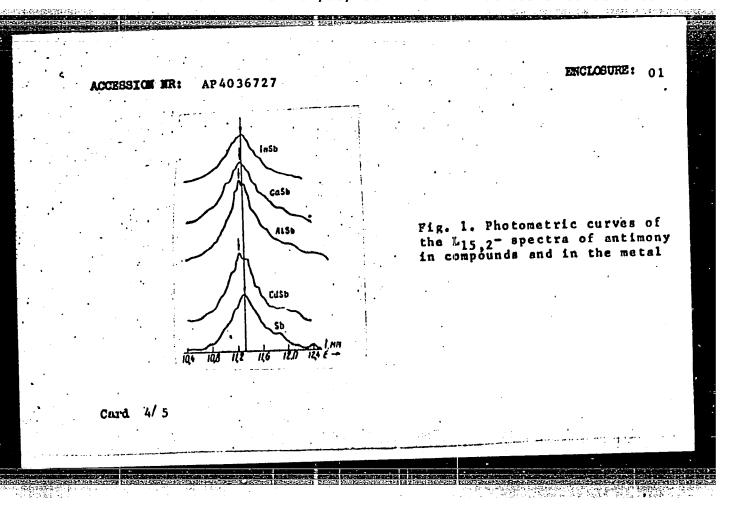
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OTHER: 005

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ACCESSION ER: AP4036727

ENCLOSURE: 02

All : 5b : Al : 5b : All : 5b : All

Sb : Al' : 55 : Al' : 5b : All

Sb : Al' : 55 : Al' : 5b : All

Fig. 2. Scheme of the chemical bonds in AIIIBV compounds exemplified by AlSb (according to the author's data)

Gard : 5/5

UGAY, Yakov Aleksandrovich; ABRIKOSOV, N.Kh., doktor khim. nauk, prof., retsenzent; GORYUNOVA, M.I., doktor khim. nauk, prof., retsenzent; FEDOROVA, T.P., red.

[Introduction to the chemistry of semiconductors] Vvedenie v khimiiu poluprovodnikov. Moskva, Vysshaia shkola, 1965. 333 p. (MIRA 18:5)

1. Kafedra poluprovodnikovykh materialov Leningradskogo politekhnicheskogo instituta im. M.I.Kalinina (for Goryunova).

"APPROVED FOR RELEASE: 04/03/2001

CIA-RDP86-00513R001857820011-8

L 2624-66 ENT(m)/EPF(c)/T/EWP(t)/EWP(b)/EWA(c) IJP(c) WR/0365/65/001/002/0190/0194

ACCESSION NR: AP5011363 UR/0365/65/001/002/0190/0194

AUTHOR: Marshakov, I. K.; Ugay, Ya. A.; Vigdorovich, V. I.

TITLE: Mechanism of corrosion of the magnesium-rinc alloys

SOURCE: Zashchita metallov, v. 1, no. 2, 1965, 190-194

TOPIC TAGS: corrosion, magnesium alloy, zinc alloy, corrosion resistence, corrosion rate

ABSTRACT: The mechanism of corrosion of magnesium-zinc alloys was studied at room temperature in 0.5-normal NaCl, 0.5-normal NaBr, and 0.1-normal HCl solutions. In corrosion tests, 12-15 ml of electrolyte was used per cm² of sample surface. The test duration was 5 hours in neutral media and 30 minutes in acidic media. Corrosion of alloys containing up to 65% Zn is very fast and is accompanied by heavy loys containing 65-72% Zn. Alloys containing more than 72% Zn corrode at a low rate and in a uniform manner. The corrosion of alloys containing up to 72% Zn is determined by the work of the phase corrosion elements: a-solid solution--inter-

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ACCESSION NR: AP5011363

metallic compound MgZn. On alloys containing 65-72% Zn, the anodic zones are small and dissolving proceeds along narrow channels between the individual grains of the intermetallic compound. Thus, the alloy material may be completely destroyed with small weight losses. Intermetallic compounds such as MgZn, MgZn₂, and MgZn₅ participate in corrosion of alloys with over 72% Zn. As a result of difference in effectiveness of the corrosion elements, the rate of corrosion in bromide solutions is smaller than in chloride solutions. The rate of alloy corrosion in 0.5-normal NaCl is shown in fig. 1 of the Enclosure. The rate of alloy corrosion in 0.1-normal HCl is shown in fig. 2 of the Enclosure. The dependence of the steady-state potentials of alloys upon their composition is shown in fig. 3 of the Enclosure. Orig. art. has: 2 tables, 5 figures.

ASSOCIATION: Voronezhskiy gosudarstvennyy universitet (Voronezh State University)

SUBMITTED: 26Sep64

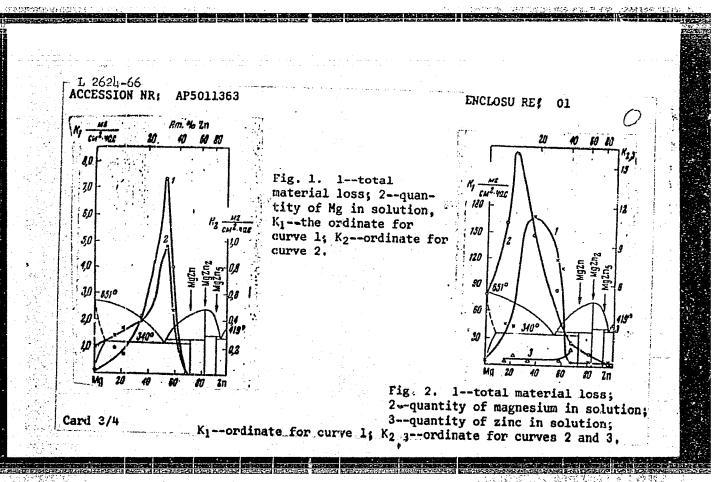
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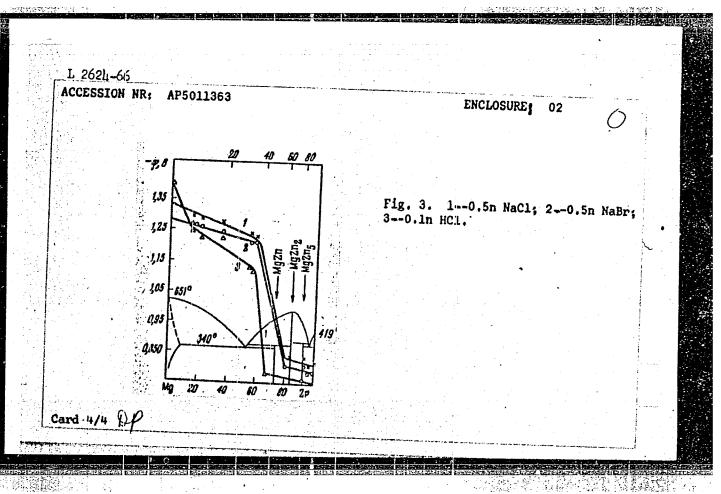
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L 2621-66 EVT(m)/EPF(c)/EVP(t)/EVP(b) IJP(c) JD/WB
ACCESSION NR: AF5011367 IVP/0365/55/601/00

UR/0365/65/001/002/0233/0235 620.193.01

AUTHOR: Shatalov, A. Ya.; Tsygankova, L. Ye.; Ugay, Ya. A.

TITLE: Anodic oxidation and corrosion resistance of indium-antimony alloys

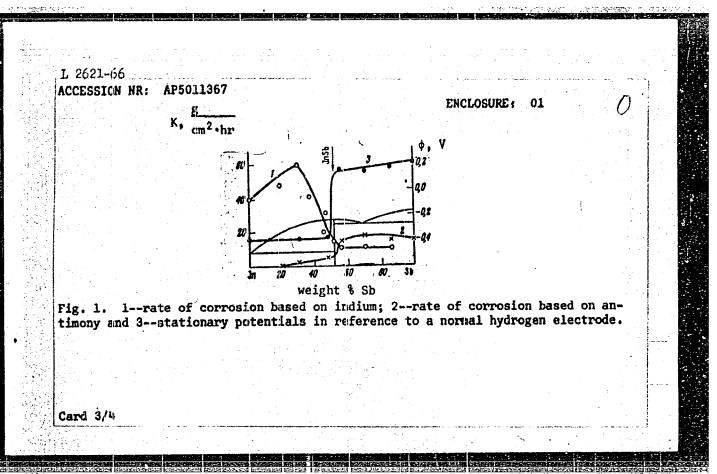
SOURCE: Zashchita metallov, v. 1, no. 2, 1965, 233-235

TOPIC TAGS: anodic oxidation, corrosion resistance, corrosion resistant alloy, antimony alloy, indium containing alloy

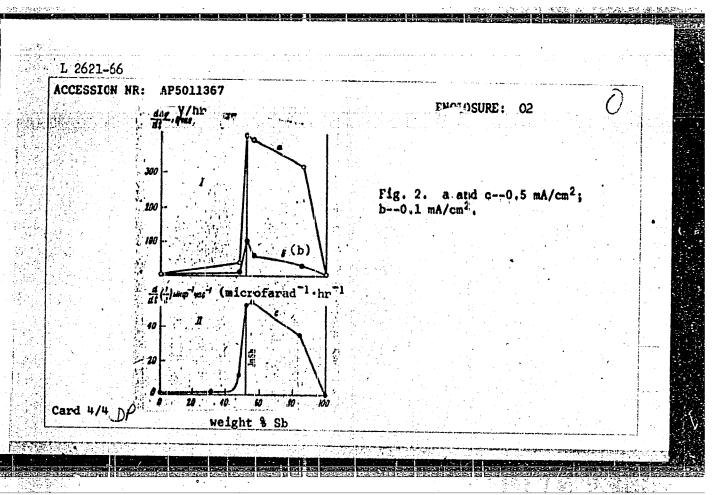
ABSTRACT: Anodic exidation and corrosion resistance of indium-antimony alloys (0-100% Sb) was studied electrochemically. The intermetallic InSb compound was prepared by means of partial melting of n- and p-type single crystals with current carrier concentrations of 3.5×10^{14} and 2.0×10^{18} , respectively. The corrosion resistance experiments were carried out in 1-normal H_2SO_4 , and in hydrogen atmosphere for 4 days. The anodic exidation process was studied in solutions with pH = 0-14 at current densities of $0.01-1 \, \text{mA/cm}^2$ using InSb single crystals. The stationary potentials and rate of corrosion of In-Sb alloys in 1-normal H_2SO_4 solution are shown in fig. 1 of the Enclosure. The maximum anodizing rate and the formation of

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L 2621-66 ACCESSION NR: AP5011367 a tight exide layer on the anode coincides with an intermetallic InSb compound containing 51.5% Sb. The dependence of the rate of anodic oxidation (I) and of (1/C) (II) in 0.ln Na₂B₄O₇ solution upon alloy composition is shown in fig. 2 đŧ of the Enclosure. The composition of the oxide layer formed on the anode containing 51.5% Sb corresponds to formula: $(In_2O_3)_7 \cdot (Sb_2O_3)$. The anodizing process is found to be independent of the type of conductivity of the anode material. Orig. art. has: 1 table, 2 figures, 1 formula. ASSOCIATION: Voronezhekiy gouudarstvennyy universitet (Voronezh State University) 14155 SUBMITTED: 03Sep64 ENCL: 02 SUB CODE: MM; GC NO REF SOV: OTHER: 001 Card 2/4



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EWT(1)/EWT(m)/T/ENP(t)/EWP(b)/EWA(h)/EWA(c) 2708-66 IJP(c) JD/AT ACCESSION NR: AP5017183 UR/0131/65/000/003/0129/0133 Ye. M.; Kruglova, G. S. 44,55 AUTHOR: Ugay, Ya. A.; Averbakh, TITLE: On the production of single crystals of semiconductor phases in the Zn-Sb system ſъ SOURCE: IVUZ. Fizika, no. 3, 1965, 129-133 TOPIC MMS: zinc alloy, antimony alloy, solid solution, single crystal growth, zone melting ABSTRACT: The authors discuss the various technical difficulties involved in the production of single crystals of inter stallic EnSb. Although they succeeded in using the Bridgman or the Chalmers method to produce single ZnSb crystals up to 12 mm long and 8 mm in diameter, drawn at a rate of 4 mm/hr, the end parts of the ingot were not monocrystalline, and the crystals contained an excess of antimony over the stoichiometric composition. It is shown, however, that such single crystals can be used as primers to grow stoichiometric ZnSb crystals by zone-melting. The technique and the properties of the grown crystals are described. It is claimed that the procedure employed conforms more closely to the properties of the Zn-Sb state diagram, is simpler, and takes less time. This technique was tried also to grow B-Zn4Sb3 single crystals, with limited success, owing to the low tem-Card 1/2